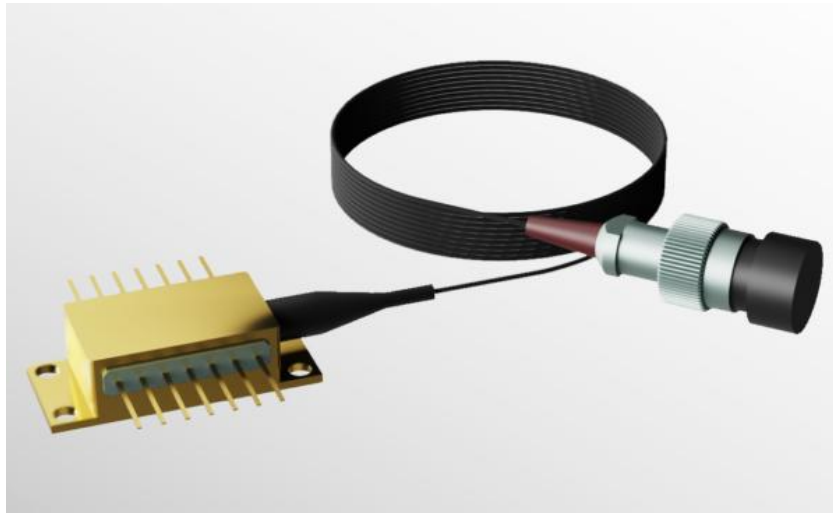


794.978 nm DBR Laser Diode



● Product Description

The 794.978 nm Distributed Bragg Reflector (DBR) high-performance edge-emitting laser diode is fabricated based on monolithic integrated single-frequency Gallium Arsenide (GaAs) laser technology. This series of diodes outputs single spatial mode laser beams, with passivated cavity facet design to guarantee device reliability. The 794.978 nm DBR device is applied for rubidium (Rb) atomic spectral analysis and quantum sensing fields. It has passed spectral certification, which can precisely match the D1 transition spectral line of rubidium within the temperature range of room temperature ± 10 °C.

● Product features

Precise matching with atomic energy level transition ; Excellent spectral performance; Professional package and integrated control interface

● Part Number

MP-DBR-794.978-60-14BF-PA

● Application area

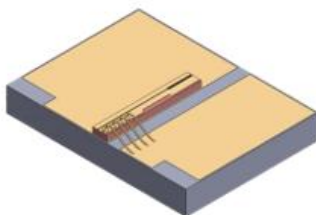
Rubidium Atomic Quantum Technology & Precision Physics |
 High-Resolution Spectroscopy

● Core parameters

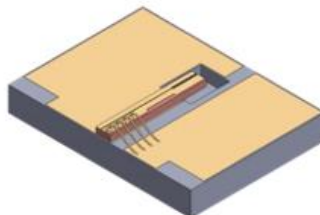
Central Wavelength
794.97nm

● General Parameters

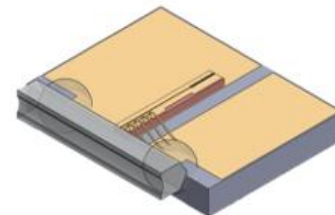
Detailed parameters



Chip on Submount (CoS)



CoS + Mode-Hop Free (MHF)



CoS + Virtual Point Source (VPS) Lens



794.978nm DBR Chip Carrier Package (CoS)

Characteristics

Parameter ¹	Chip structure		
	HOT ³ (High Operating Temperature).	Low power	High power
Nominal wavelength (nm) ²	794.978 ± 0.6		
Power range	10-30	40-80	80-180
Maximum Operating Current (CW & Pulse) (mA)	80	140	250
Maximum Operating Current Hour Power (mW)	30	80	180
Nominal Slope Efficiency (W/A)	0.6	0.9	0.85
Nominal threshold current (mA)	30	30	60

1. Unless otherwise stated, all characteristics are measured at a case temperature (TC) of 25°C. Operating outside of these parameters will void the warranty.
2. The sealed package may contain a chip carrier (CoS) with a wavelength deviation of ±1.2 nm from the nominal value.
3. The high-temperature (HOT) characteristic parameter is performed at 65°C.

Available free-space encapsulation add-ons



9MM



TO-8



C-Mount



Transmitter Optical Subassembly (TOSA)

Parameters

Laser

Parameters	unit	Minimum	Typical values	Maximum
Storage temperature	°C	0	-	70
Shell operating temperature	°C	5	-	70
The laser chip operating temperature ¹	°C	5	-	45
Laser series resistance	Ω	-	2	-
Laser forward voltage @LIV current	V	-	2	-
Laser line width, typical @LIV current	kHz	-	500	-
Beam Divergence Angle @FWHM ($\theta_{ }$ x θ_{\perp})	°	-	6x28	8 x 32
Edge-mode rejection ratio (SMSR)	dB	-	-40	-
Polarization extinction ratio	dB	-17	-20	-
Polarized state of the laser	TE			
Pattern structure	Fundamental mode			
Temperature tuning rate	nm/°C	-	0.06	-
Current tuning rate	nm/mA	-	0.002	-
Laser reverse voltage	V	-	-	0

1. If the package is not sealed, it is not recommended to work in an environment below the dew point

Free space encapsulation add-ons

Parameters	unit	Minimum	Typical values	Maximum
Photodiode forward current	mA	-	-	10
Photodiode reverse voltage	V	-	-	50
TEC Current (TOSA)	A	-1.1	-	1.1
TEC Voltage (TOSA)	V	-3.0	-	3.0
TEC Current (TO-8)	A	-1.8	-	1.8
TEC Voltage (TO-8)	V	-2.2	-	2.2
Thermistors	kΩ	-	10	-

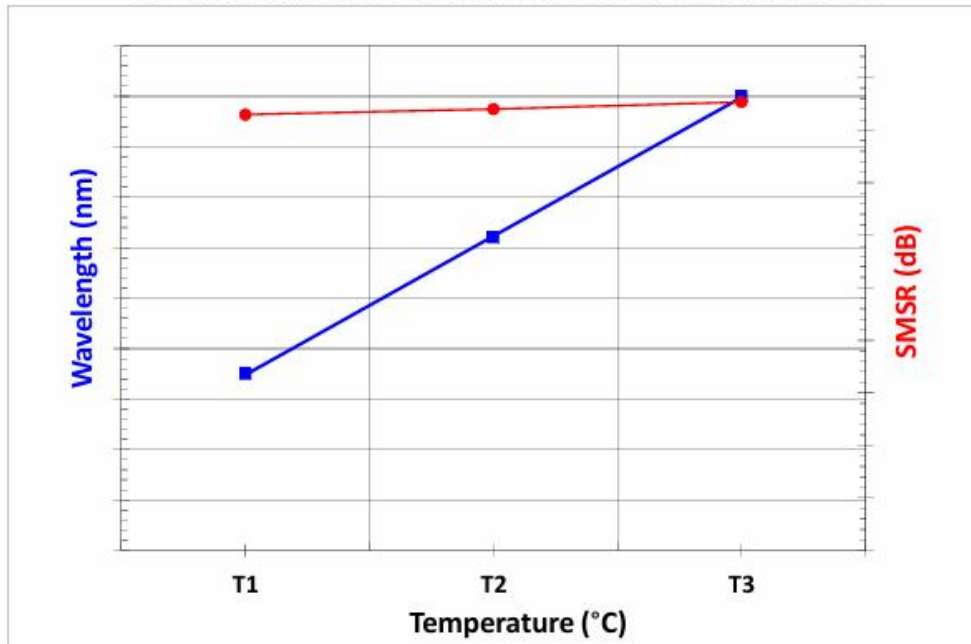
Handling Precautions

These devices are sensitive to ESD. When handling the module, grounded work area and wrist strap must be used. Always store in an antistatic container with all leads shorted together.





Air Wavelength Characteristics at Constant Current by Temperature



LIV Characteristics by Current

